

TC74VHC373F, TC74VHC373FW, TC74VHC373FT

OCTAL D-TYPE LATCH WITH 3-STATE OUTPUT

The TC74VHC373 is an advanced high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This 8-bit D-type latch is controlled by a latch enable input (LE) and an output enable input ($\overline{OE}$).

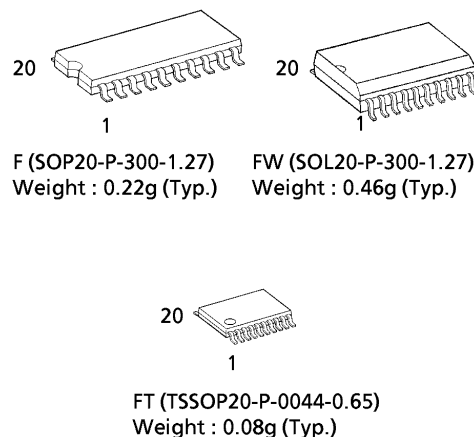
When the $\overline{OE}$ input is high, the eight outputs are in a high impedance state.

An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

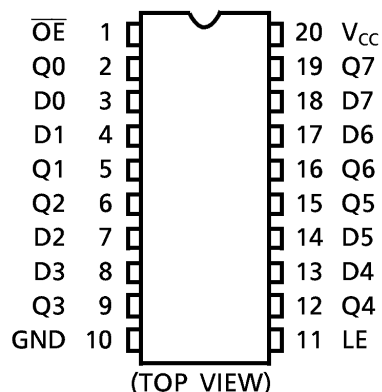
FEATURES:

- High Speed..... $t_{pd} = 5.0ns(typ.)$ at $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 4\mu A(Max.)$ at $T_a = 25^\circ C$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC} (Min.)$
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range..... $V_{CC} (opr) = 2V \sim 5.5V$
- Low Noise..... $V_{OLP} = 0.9V (Max.)$
- Pin and Function Compatible with 74ALS373

(Note) The JEDEC SOP (FW) is not available in Japan.



PIN ASSIGNMENT



TRUTH TABLE

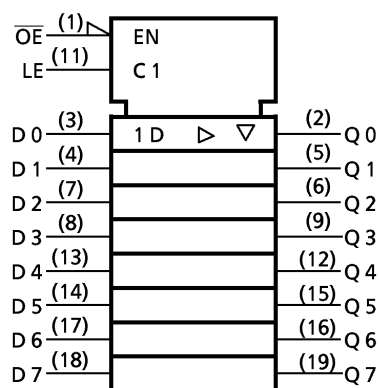
INPUTS			OUTPUT
$\overline{OE}$	LE	D	
H	X	X	Z
L	L	X	Q_n
L	H	L	L
L	H	H	H

X : Don't Care

Z : High Impedance

Q_n : Q outputs are latched at the time when the LE input is taken to a low logic level.

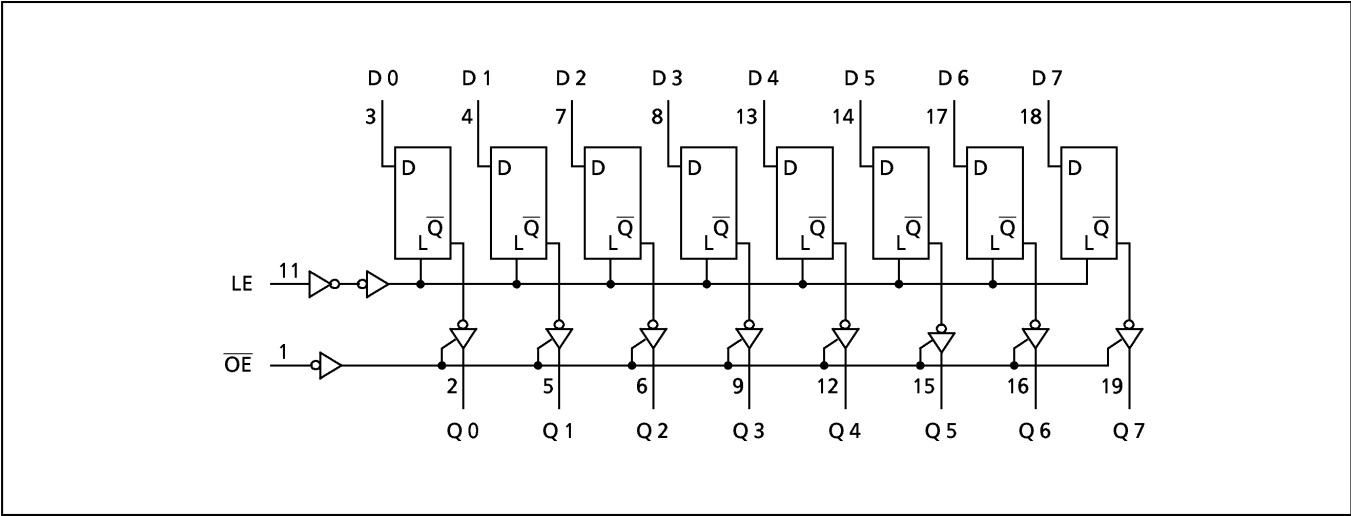
IEC LOGIC SYMBOL



961001EBA2

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SYSTEM DIAGRAM



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7.0$	V
DC Input Voltage	V_{IN}	$-0.5 \sim 7.0$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	-20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} /Ground Current	I_{CC}	± 75	mA
Power Dissipation	P_D	180	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	$^{\circ}\text{C}$

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2.0~5.5	V
Input Voltage	V_{IN}	0~5.5	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	$-40 \sim 85$	$^{\circ}\text{C}$
Input Rise and Fall Time	dt/dv	0~100 ($V_{CC} = 3.3 \pm 0.3\text{V}$) 0~20 ($V_{CC} = 5 \pm 0.5\text{V}$)	ns/V

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DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION		V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
					MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V _{IH}			2.0 3.0~5.5	1.50 V _{CC} × 0.7	— —	— —	1.50 V _{CC} × 0.7	— —	V
Low - Level Input Voltage	V _{IL}			2.0 3.0~5.5	— —	— —	0.50 V _{CC} × 0.3	— —	0.50 V _{CC} × 0.3	V
High - Level Output Voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5	— — —	1.9 2.9 4.4	— — —	V
			I _{OH} = -4mA I _{OH} = -8mA	3.0 4.5	2.58 3.94	— —	— —	2.48 3.80	— —	
Low - Level Output Voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50μA	2.0 3.0 4.5	— — —	0.0 0.0 0.0	0.1 0.1 0.1	— — —	0.1 0.1 0.1	V
			I _{OL} = 4mA I _{OL} = 8mA	3.0 4.5	— —	— —	0.36 0.36	— —	0.44 0.44	
3 - State Output Off - State Current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND		5.5	—	—	± 0.25	—	± 2.50	μA
Input Leakage Current	I _{IN}	V _{IN} = 5.5V or GND		0~5.5	—	—	± 0.1	—	± 1.0	
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND		5.5	—	—	4.0	—	40.0	

TIMING REQUIREMENTS (Input t_r = t_f = 3ns)

PARAMETER	SYMBOL	TEST CONDITION		V _{CC} (V)	Ta = 25°C		Ta = -40~85°C	UNIT
					TYP .	LIMIT	LIMIT	
Minimum Pulse Width (LE)	t _W (H)			3.3 ± 0.3 5.0 ± 0.5	— —	5.0 5.0	5.0 5.0	ns
Minimum Set - up Time	t _s			3.3 ± 0.3 5.0 ± 0.5	— —	4.0 4.0	4.0 4.0	
Minimum Hold Time	t _h			3.3 ± 0.3 5.0 ± 0.5	— —	1.0 1.0	1.0 1.0	

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL		TEST CONDITION		Ta = 25°C			Ta = − 40~85°C		UNIT
			V _{CC} (V)	CL (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time (LE-Q)	t _{pLH} t _{pHL}		3.3 ± 0.3	15	—	7.0	11.0	1.0	13.0	ns
				50	—	9.5	14.5	1.0	16.5	
			5.0 ± 0.5	15	—	4.9	7.2	1.0	8.5	
				50	—	6.4	9.2	1.0	10.5	
Propagation Delay Time (D-Q)	t _{pLH} t _{pHL}		3.3 ± 0.3	15	—	7.3	11.4	1.0	13.5	
				50	—	9.8	14.9	1.0	17.0	
			5.0 ± 0.5	15	—	5.0	7.2	1.0	8.5	
				50	—	6.5	9.2	1.0	10.5	
3-State Output Enable Time	t _{pZL} t _{pZH}	RL = 1kΩ	3.3 ± 0.3	15	—	7.3	11.4	1.0	13.5	
				50	—	9.8	14.9	1.0	17.0	
			5.0 ± 0.5	15	—	5.5	8.1	1.0	9.5	
				50	—	7.0	10.1	1.0	11.5	
3-State Output Disable Time	t _{pLZ} t _{pHZ}	RL = 1kΩ	3.3 ± 0.3	50	—	9.5	13.2	1.0	15.0	
			5.0 ± 0.5	50	—	6.5	9.2	1.0	10.5	
Output to Output Skew	t _{osLH} t _{osHL}	(Note 1)	3.3 ± 0.3	50	—	—	1.5	—	1.5	
			5.0 ± 0.5	50	—	—	1.0	—	1.0	
Input Capacitance	C _{IN}				—	4	10	—	10	pF
Output Capacitance	C _{OUT}				—	6	—	—	—	
Power Dissipation Capacitance	C _{PD}	(Note 2)			—	27	—	—	—	

Note (1) Parameter guaranteed by design. $t_{\text{osLH}} = |t_{\text{pLH m}} - t_{\text{pLH n}}|$, $t_{\text{osHL}} = |t_{\text{pHL m}} - t_{\text{pHL n}}|$

Note (2) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{\text{CC(opr.)}} = C_{\text{PD}} \cdot V_{\text{CC}} \cdot f_{\text{IN}} + I_{\text{CC}}/8 \text{ (per latch)}$$

And the total C_{PD} when n pcs. of Latch operate can be gained by the following equation :

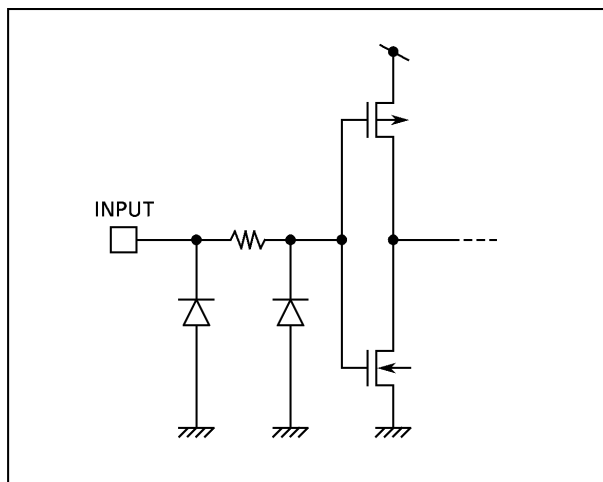
$$C_{\text{PD}} \text{ (total)} = 14 + 13 \cdot n$$

NOISE CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			UNIT
			V _{CC} (V)	TYP.	MAX.	
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	C _L = 50pF	5.0	0.5 (0.6)	0.8 (0.9)	V
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	C _L = 50pF	5.0	-0.5 (-0.6)	-0.8 (-0.9)	V
Minimum High Level Dynamic Input Voltage	V _{IHD}	C _L = 50pF	5.0	—	3.5	V
Maximum Low Level Dynamic Input Voltage	V _{ILD}	C _L = 50pF	5.0	—	1.5	V

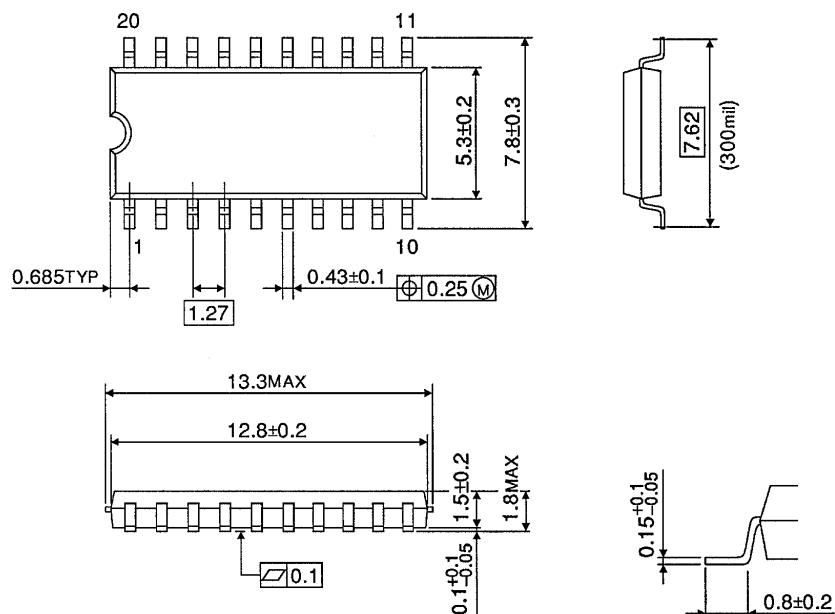
(Note) The value in () only applies to JEDEC SOP (FW) devices.

INPUT EQUIVALENT CIRCUIT



SOP 20PIN (200mil BODY) OUTLINE DRAWING (SOP20-P-300-1.27)

Unit in mm

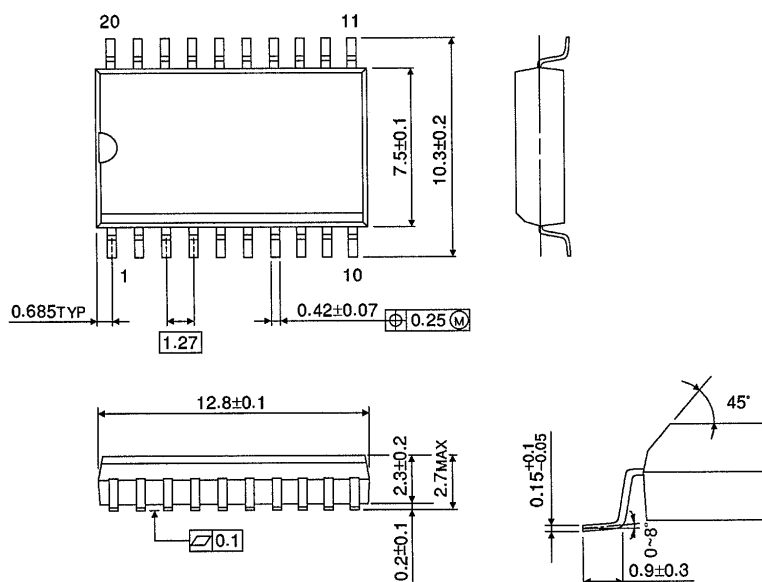


Weight : 0.22g (Typ.)

SOP 20PIN (300mil BODY) OUTLINE DRAWING (SOP20-P-300-1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.46g (Typ.)

TSSOP 20PIN OUTLINE DRAWING (TSSOP20-P-0044-0.65)

Unit in mm

